

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masahiro KANAI

Application No.: New US Application

Filed: February 18, 2004

Docket No.: 118739

For: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE
INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the references Nos. 1-3 and 11-12 is discussed in the present specification.
- ☒ 3. The present application was filed or entered the U.S. National Stage of the PCT after June 30, 2003. In accordance with the June 11, 2003, Notice waiving the requirements of 37 C.F.R. §1.98(a)(2)(i), copies of any U.S. patents and patent application publications are not attached.
- ☒ 4. English-language Abstracts of the non-English language references Nos. 8-12 are attached hereto.
- ☒ 5. A computer-generated English translation of the following Japanese Patent Publication has been obtained from the website of the Japanese Patent Office (<http://www.jpo.go.jp>), and is attached, but has not been reviewed for accuracy. See References 8-10.
- ☒ 6. References 11 and 2 correspond to each other.

Respectfully submitted,



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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 118739		APPLICATION NO. New US Application	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Masahiro KANAI			
				FILING DATE February 18, 2004			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
	1	6,255,166 B1	07/03/2001	Ogura et al.			
	2	5,408,115	04/18/1995	Chang			
	3	5,969,383	10/19/1999	Chang et al.			
	4	5,422,504	06/06/1995	Chang et al.			
	5	5,494,838	02/27/1996	Chang et al.			
	6	6,177,318 B1	01/23/2001	Ogura et al.			
	7	6,248,633 B1	06/19/2001	Ogura et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
	8	JP B1 2978477 (with abstract and translation)	09/10/1999	Japan			
	9	JP A 7-161851 (with abstract and translation)	06/23/1995	Japan			
	10	JP A 2001-156188 (with abstract and translation)	06/08/2001	Japan			
	11	JP A 6-181319 (with abstract)	06/28/1994	Japan			
	12	JP A 11-74389 (with abstract)	03/16/1999	Japan			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
	13	Hayashi et al. "Twin MONOS Cell with Dual Control Gates", 2000 Symposium on VLSI Technology Digest of Technical Papers					
	14	Chang et al. "A New SONOS Memory using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, July 1998, pp 253-255					
	15	Chen et al. "A Novel Flash Memory Device with S Plit Gate Source Side Injection and ONO Charge Storage Stack (SPIN), 1997 Symposium on VLSI Technology Digest of Technical Papers, pp 63-64					
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: February 18, 2004